

# MA2C185

## Silicon epitaxial planar type

For high-voltage switching circuits, small power rectification

### ■ Features

- High reverse voltage ( $V_R = 200\text{ V}$ )
- Large output current  $I_O$
- Small glass type (DO-34) package, allowing to insert into a 5 mm pitch hole

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	200	V
Repetitive peak reverse voltage	$V_{RRM}$	250	V
Output current	$I_O$	200	mA
Repetitive peak reverse current	$I_{FRM}$	625	mA
Non-repetitive peak forward surge current surge current*	$I_{FSM}$	1	A
Average power dissipation	$P_{F(AV)}$	400	mW
Junction temperature	$T_j$	175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$

Note) \* :  $t = 1\text{ s}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 200\text{ V}$			200	nA
Forward voltage (DC)	$V_F$	$I_F = 200\text{ mA}$			1.2	V
Reverse voltage (DC)	$V_R$	$I_R = 100\ \mu\text{A}$	250			V
Terminal capacitance	$C_t$	$V_R = 0\text{ V}, f = 1\text{ MHz}$		4.5		pF

Note) Rated input/output frequency: 3 MHz

### ■ Cathode Indication

Type No.	MA2C185	
Color	1st Band	White
	2nd Band	Green



